What is claimed is:

1. A semiconductor fabrication process, comprising:

providing a coated article, the coated article having a substrate and a layer applied to the substrate by decomposition and then oxidization of dimethylsilane through chemical vapor deposition, the layer applied by a fluid material, wherein the layer includes trimethylsilane applied to the oxidized dimethylsilane; and then

positioning the coated article in a system for producing a semiconductor product.

2. The process of claim 1, wherein the fluid material is a gas.

3. The process of claim 1, wherein the coated article is a tube and the layer is an internal surface of the tube, the coated article is a fitting and the layer is an internal surface of the fitting, the coated article is a pipe and the layer is an internal surface of the pipe, or the coated article is a chamber and the layer is an internal surface of the chamber wall.

4. The process of claim 1, wherein the semiconductor product comprises a crystalline solid, a poly-crystalline material, or an amorphous material.

5. The process of claim 1, wherein the semiconductor product includes an intrinsic semiconductor.

6. The process of claim 1, wherein the semiconductor product includes an extrinsic semiconductor having a positive charge conductor.

7. The process of claim 1, wherein the semiconductor product is selected from the group consisting of a pure element semiconductor and a compound semiconductor.

8. The process of claim 1, wherein the semiconductor product includes a surface consisting of indium antimonide (InSb), indium arsenide (InAs), indium phosphide (InP), gallium phosphide (GaP), gallium antimonide (GaSb), gallium arsenide (GaAs), silicon carbide (SiC), gallium nitride (GaN), silicon germanium (SiGe), or selenium sulfide (SeS).